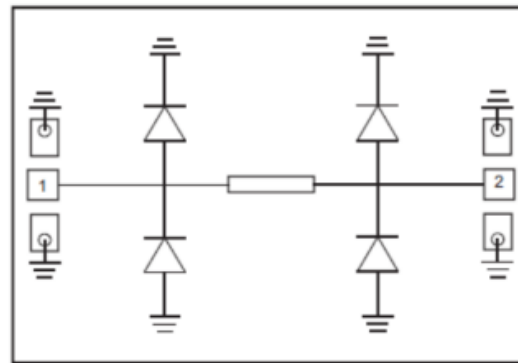


Features

- Frequency:1-4GHz
- Insertion Loss: 0.3dB (typ.)
- Limit Power:13dBm
- Tolerance Power:45dBm(CW)
- Input/Output: 50Ω
- Die Size: 1.72x0.8x 0.1 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

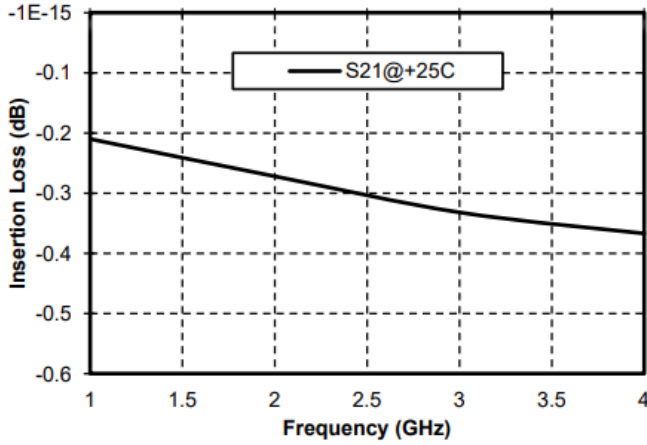
Functional Block Diagram

Electrical Specifications

TA = +25°C

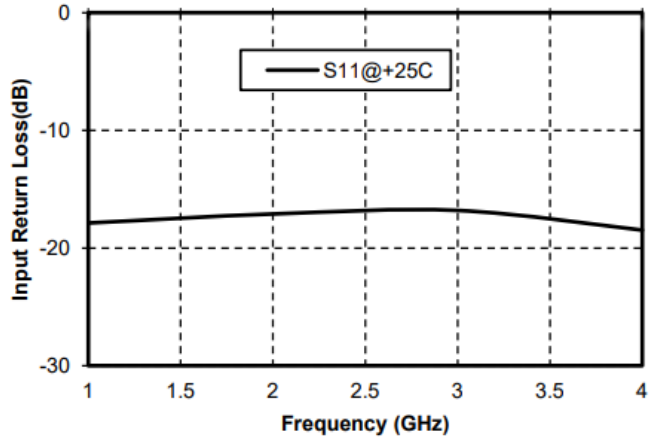
Parameters	Min.	Typ.	Max.	Units
Frequency	1-4			GHz
Insertion Loss	-	0.3	0.4	dB
Input Return Loss	17	17	-	dB
Output Return Loss	17	18	-	dB
Limit Power	-	13	-	dBm
Tolerance Power		45		dBm



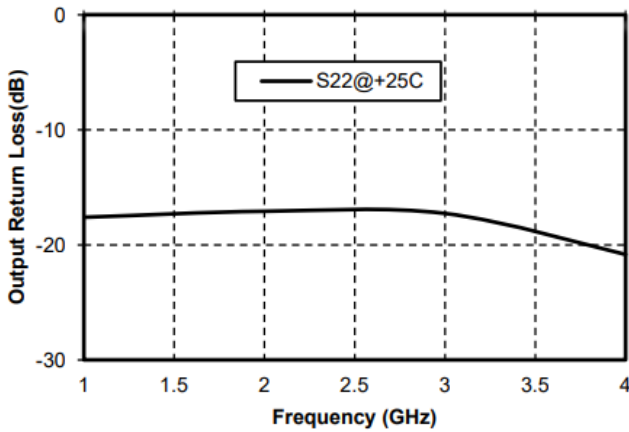
Insertion Loss Vs. Frequency



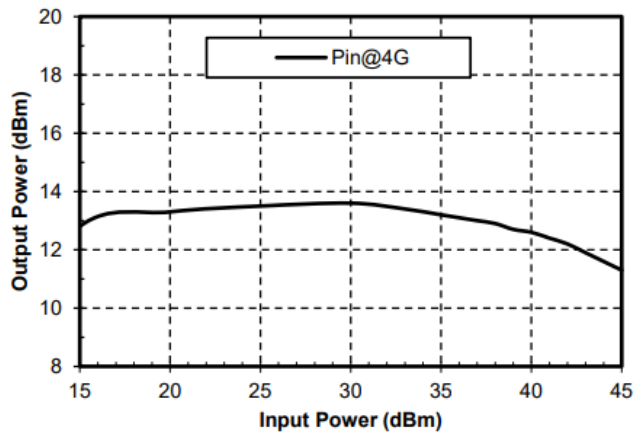
Input Return Loss Vs. Frequency



Output Return Loss Vs. Frequency



Limit Power @4G





Outline Drawing:

All Dimensions in um, tolerance range $\pm 50\mu\text{m}$



Pad Description

PAD	Function	Description
1	RF IN	RF signal input, no DC blocking capacitor integrated at the chip input, external DC-blocking capacitor required
2	RF OUTPUT	RF signal output, A DC blocking capacitor has been integrated at the output of the chip
Die Bottom	GND	Die bottom must be connected to RF/DC ground.



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +45dBm
2. Storage temperature: -65°C to +150°C
3. Operating temperature: -55°C to 125°C